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03714121 **Image available**
MANUFACTURE OF SEMICONDUCTOR DEVICE

PUB. NO.: 04-079221 [JP 4079221 A]
PUBLISHED: March 12, 1992 (19920312)
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APPL. NO.: 02-192712 [JP 90192712]
FILED: July 20, 1990 (19900720)
INTL CLASS: [5] H01L-021/304
JAPIO CLASS: 42.2 (ELECTRONICS -- Solid State Components)
JOURNAL: Section: E, Section No. 1226, Vol. 16, No. 297, Pg. 11, June 30, 1992 (19920630)

ABSTRACT

PURPOSE: To reduce cost, to improve producibility and to stabilize quality of a semiconductor device by cleaning a substrate surface while adding gas containing ozone to ammonia water solution.

CONSTITUTION: Mixture solution 104 of aqueous ammonia and pure water is heated by a heater 102 in a chemical solution tank 101. Gas containing ozone such as mixture gas 106 of ozone and oxygen is let out of a tube 105 which is introduced below the chemical tank 101 and is made to impinge on the surface of an Si substrate 103 for cleaning.

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